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11-A

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/761,575	01/21/2004	Yuegang Zhang	ITL.1076US (P18261)	2608

21906 7590 05/21/2007
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HOUSTON, TX 77057-2631

EXAMINER

PHAM, THANHHA S

ART UNIT	PAPER NUMBER
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2813

MAIL DATE	DELIVERY MODE
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05/21/2007

PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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APPLICATION NO./ CONTROL NO.	FILING DATE	FIRST NAMED INVENTOR / PATENT IN REEXAMINATION	ATTORNEY DOCKET NO.
10761575	1/21/04	ZHANG, YUEGANG	ITL.1076US (P18261)

EXAMINER

Thanhha Pham

ART UNIT	PAPER
2813	20070502

DATE MAILED:

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner for Patents

The reply brief filed 03/26/2007 has been entered and considered. The application has been forwarded to the Board of Patent Appeals and Interferences for decision on the appeal. The argument is not persuasive since the rejection and the argument clearly explains the plural carbon nanotubes having functionalized ends with attached functional groups (carbon nanotubes 2 having ends being made to function as electrical connection or being caused to be functional in transistor operation when the ends of the carbon nanotube 2 being attached with functional groups of source and drain 3 & 4 for transistor operation). Plefferle is one of previously applied prior arts as an evidence that shows usages of open-ended (capless) nanotubes in transistor.

**THANHHA S. PHAM
PRIMARY EXAMINER**